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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# MOS FIELD EFFECT TRANSISTOR $\mu$ PA1763

## SWITCHING DUAL N-CHANNEL POWER MOS FET INDUSTRIAL USE

#### **DESCRIPTION**

The  $\mu$ PA1763 is N-Channel MOS Field Effect Transistor designed for DC/DC Converters.

#### **FEATURES**

- Dual chip type
- · Low on-resistance

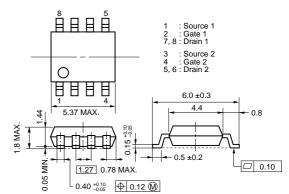
RDS(on)1 = 47.0 m $\Omega$  MAX. (Vgs = 10 V, ID = 2.3 A)

 $R_{DS(on)2} = 57.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.5 \text{ V, Ip} = 2.3 \text{ A)}$ 

 $R_{DS(on)3} = 66.0 \text{ m}\Omega$  MAX. (Vgs = 4.0 V, ID = 2.3 A)

- Low input capacitance
  - $C_{iss} = 870 pF TYP.$
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

## PACKAGE DRAWING (Unit : mm)



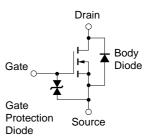
## **ORDERING INFORMATION**

PART NUMBER	PACKAGE
μPA1763G	Power SOP8

## ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, All terminals are connected.)

Drain to Source Voltage	VDSS	60	V	
Gate to Source Voltage	Vgss	±20	V	ı
Drain Current (DC)	ID(DC)	±4.5	Α	!
Drain Current (pulse) Note1	D(pulse)	±18	Α	
Total Power Dissipation (1 unit) Note2	PT	1.7	W	
Total Power Dissipation (2 unit) Note2	PT	2.0	W	
Single Avalanche Current Note3	las	4.5	Α	
Single Avalanche Energy Note3	Eas	60	mJ	
Channel Temperature	Tch	150	°C	
Storage Temperature	T <sub>stg</sub>	-55 to + 150	°C	

## EQUIVALENT CIRCUIT (1/2 Circuit)



- **Notes 1.** PW  $\leq$  10  $\mu$ s, Duty cycle  $\leq$  1 %
  - **2.**  $T_A = 25$  °C, Mounted on ceramic substrate of 1200 mm<sup>2</sup> x 2.2 mm
  - 3. Starting Tch = 25 °C, Rg = 25  $\Omega$ , Vgs = 20 V  $\rightarrow$  0 V

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage Exceeding the rated voltage may be applied to this device.

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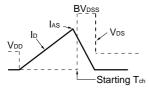


## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, All terminals are connected.)

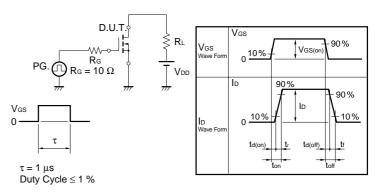
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, lb = 2.3 A		37.0	47.0	mΩ
	RDS(on)2	Vgs = 4.5 V, ID = 2.3 A		45.0	57.0	mΩ
	RDS(on)3	Vgs = 4.0 V, ID = 2.3 A		49.0	66.0	mΩ
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.3 A	3.0	6.0		S
Drain Leakage Current	IDSS	Vps = 60 V, Vgs = 0 V			10	μΑ
Gate to Source Leakage Current	Igss	Vgs = ±16 V, Vps = 0 V			±10	μΑ
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V		870		pF
Output Capacitance	Coss	Vgs = 0 V		150		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		80		pF
Turn-on Delay Time	<b>t</b> d(on)	ID = 2.3 A		11		ns
Rise Time	tr	V <sub>GS(on)</sub> = 10 V		40		ns
Turn-off Delay Time	td(off)	VDD = 30 V		50		ns
Fall Time	t <sub>f</sub>	$R_G = 10 \Omega$		12		ns
Total Gate Charge	Q <sub>G</sub>	ID = 4.5 A		20		nC
Gate to Source Charge	Qgs	V <sub>DD</sub> = 48 V		3		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>G</sub> S = 10 V		5		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	IF = 4.5 A, VGS = 0 V		0.80		V
Reverse Recovery Time	trr	IF = 4.5 A, VGS = 0 V		30		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		40		nC

## **TEST CIRCUIT 1 AVALANCHE CAPABILITY**

# $\begin{array}{c} \text{D.U.T.} \\ \text{RG} = 25 \Omega \\ \text{VGS} = 20 \rightarrow 0 \text{ V} \\ \end{array} \begin{array}{c} \text{PG.} \\ \text{$\stackrel{>}{>}$} 50 \Omega \\ \text{$\stackrel{>}{>}$} \end{array} \begin{array}{c} \text{Vob} \\ \text{$\stackrel{>}{>}$} \end{array}$



## **TEST CIRCUIT 2 SWITCHING TIME**

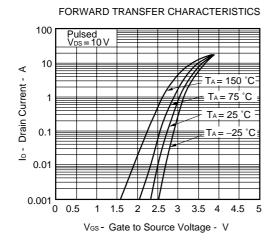


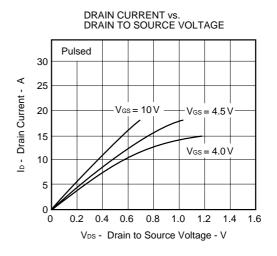
## **TEST CIRCUIT 3 GATE CHARGE**

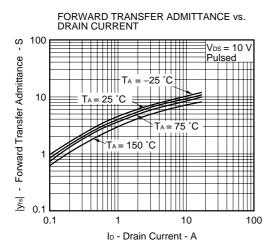
$$\begin{array}{c|c} D.U.T. \\ \hline \\ I_G = 2 \text{ mA} \\ \hline \\ \hline \\ PG. \\ \hline \\ \end{array} \begin{array}{c} S_{DL} \\ \hline \\ \\ \hline \\ \\ \end{array} \begin{array}{c} R_L \\ \hline \\ \\ \\ \end{array}$$

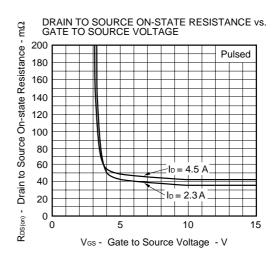


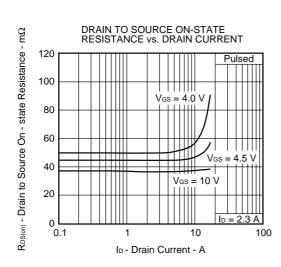
## TYPICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

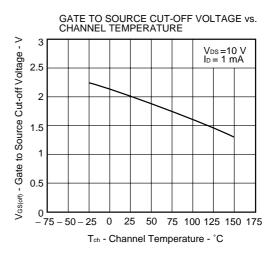




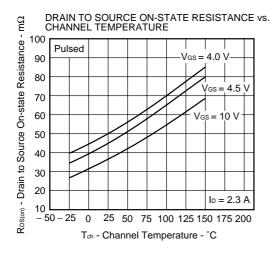


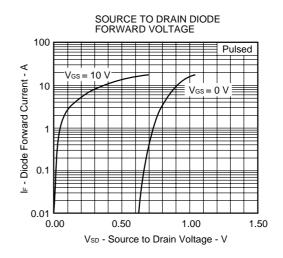


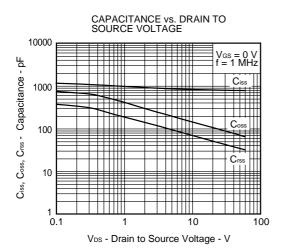


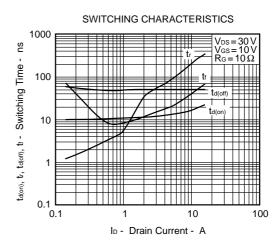


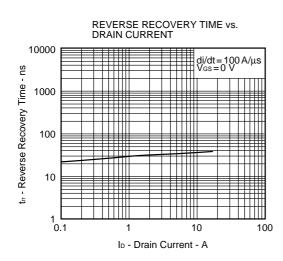
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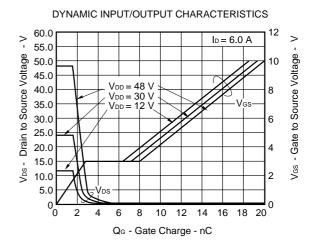


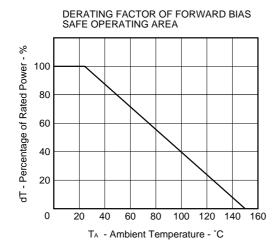


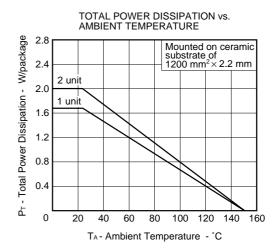




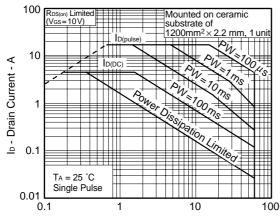






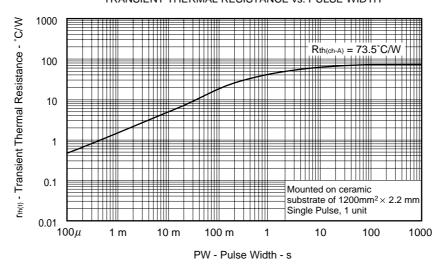


## ★ FORWARD BIAS SAFE OPERATING AREA

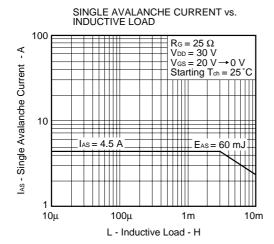


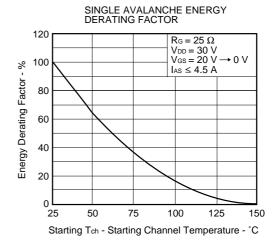
VDS - Drain to Source Voltage - V

## TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



5





NEC  $\mu$ PA1763

[MEMO]

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